

In the Claims:

Please cancel claims 24 and 31-32. Please amend claims 10-11 and 28-29. Please add new claims 34-36. The claims are as follows.

Claims 1-9 (CANCELED)

10. (CURRENTLY AMENDED) A method for forming an electronic structure, comprising the following steps:

providing a metallic plate such that all exterior surfaces of the metallic plate are exposed to an ambient atmosphere;

forming a mineral layer on the metallic plate after the step of providing a metallic plate is performed, including forming a first portion of the mineral layer on a first surface of the metallic plate and forming a second portion of the mineral layer on a second surface of the metallic plate, wherein the first surface of the metallic plate is about perpendicular to the second surface of the metallic plate; and

forming an adhesion promoter layer on the mineral layer after the step of forming a mineral layer is performed, including forming a first portion of the adhesion promoter layer on the first portion of the mineral layer and forming a second portion of the adhesion promoter layer on the second portion of the mineral layer.

11. (CURRENTLY AMENDED) The method of claim 10 A method for forming an electronic structure, comprising the following steps:

providing a metallic plate such that all exterior surfaces of the metallic plate are exposed to an ambient atmosphere;

forming a mineral layer on the metallic plate after the step of providing a metallic plate is performed; and

forming an adhesion promoter layer on the mineral layer after the step of forming a mineral layer is performed, wherein forming the mineral layer includes forming the mineral layer having a mineral selected from the group consisting of silicon dioxide, silicon nitride, and silicon carbide.

12. (PREVIOUSLY PRESENTED) The method of claim 10, wherein forming the mineral layer includes forming the mineral layer having a thickness between about 50 angstroms and about 2000 angstroms.

13. (PREVIOUSLY PRESENTED) The method of claim 10, wherein forming the mineral layer includes sputtering the mineral layer on a clean surface of the metallic plate.

14. (PREVIOUSLY PRESENTED) The method of claim 10, wherein providing the metallic plate includes providing the metallic plate having a metallic substance selected from the group consisting of stainless steel, aluminum, titanium, copper, copper coated with nickel, and copper coated with chrome.

15. (PREVIOUSLY PRESENTED) The method of claim 10, wherein forming the adhesion promoter layer includes forming the adhesion promoter layer having an adhesion promoter selected from the group consisting of a titanate, a zirconate, and an aluminate.

16. (PREVIOUSLY PRESENTED) The method of claim 10, wherein forming the adhesion promoter layer includes forming the adhesion promoter layer having a silane from the group consisting of 3-glycidoxypolytrimethoxysilane, 3-glycidoxypolytriethoxysilane, 3-(2-aminoethyl)propyltrimethoxysilane, and 3-(2-aminoethyl)propyltrimethoxysilane.

17. (ORIGINAL) The method of claim 10, further comprising:

- providing an electronic assembly;
- providing an adhesive material;
- coupling the metallic plate to the electronic assembly by interfacing the adhesive material between the adhesion promoter layer and the electronic assembly;
- providing an electronic carrier;
- coupling the electronic assembly to the electronic carrier; and
- coupling the metallic plate to the electronic carrier by interfacing the adhesive material between the adhesion promoter layer and the electronic carrier.

18-19. (CANCELED)

20. (PREVIOUSLY PRESENTED) The method of claim 10, further comprising bonding the

adhesion promoter layer to a structural adhesive.

21. (PREVIOUSLY PRESENTED) The method of claim 10, wherein the adhesion promoter layer has a thickness between 1 monolayer and about 50 monolayers.

22. (PREVIOUSLY PRESENTED) The method of claim 10, wherein forming the adhesion promoter layer includes forming the adhesion promoter layer comprising a chemical compound in crystalline form.

23. (PREVIOUSLY PRESENTED) The method of claim 10, wherein forming the adhesion promoter layer includes forming the adhesion promoter layer comprising a chemical compound in amorphous form.

24. (CANCELED)

25. (PREVIOUSLY PRESENTED) The method of claim 10, wherein forming the mineral layer includes forming the mineral layer having a thickness between about 100 angstroms and about 1000 angstroms.

26. (CANCELED)

27. (PREVIOUSLY PRESENTED) The method of claim 10, wherein forming the adhesion

promoter layer includes forming the adhesion promoter layer having an adhesion promoter comprising a silane.

28. (CURRENTLY AMENDED) A method for forming an electronic structure, comprising the following steps performed:

- providing a metallic plate such that all exterior surfaces of the metallic plate are exposed to an ambient atmosphere;
- bonding a mineral layer to the metallic plate; and The method of claim 10, wherein the step of forming an adhesion promoter layer comprises covalently bonding an the adhesion promoter layer to the mineral layer.

29. (CURRENTLY AMENDED) A method for forming an electronic structure, comprising the following steps performed:

- providing a metallic plate such that all exterior surfaces of the metallic plate are exposed to an ambient atmosphere;
- bonding a mineral layer to the metallic plate; and The method of claim 10, wherein the step of forming an adhesion promoter layer comprises bonding an the adhesion promoter layer to the mineral layer such that said bonding to the mineral layer is moisture resistant.

30-32.(CANCELED)

33. (PREVIOUSLY PRESENTED) The method of claim 10, wherein the step of forming the

mineral layer on the metallic plate comprises forming the mineral layer on first and second exposed surface of said exposed surfaces, and wherein said first and second exposed surfaces are not coplanar.

34. (NEW) The method of claim 10,

wherein the step of forming a mineral layer on the metallic plate further includes forming a third portion of the mineral layer on a third surface of the metallic plate,

wherein the third surface of the metallic plate is about perpendicular to the second surface of the metallic plate,

wherein the third surface of the metallic plate is about parallel to the first surface of the metallic plate, and

wherein the step of forming an adhesion promoter layer on the mineral layer further includes forming a third portion of the adhesion promoter layer on the third portion of the mineral layer.

35. (NEW) The method of claim 17, wherein the electronic assembly is a semiconductor chip, and wherein the electronic carrier is a chip carrier.

36. (NEW) A method for forming an electronic structure, comprising the steps of:

providing a metallic plate such that all exterior surfaces of the metallic plate are exposed to an ambient atmosphere;

forming a mineral layer on the metallic plate after the step of providing a metallic plate is

performed;

forming an adhesion promoter layer on the mineral layer after the step of forming a mineral layer is performed

providing a semiconductor chip;

providing an adhesive material;

coupling the metallic plate to the semiconductor chip by interfacing the adhesive material between the adhesion promoter layer and the semiconductor chip;

providing a chip carrier;

coupling the semiconductor chip to the chip carrier; and

coupling the metallic plate to the chip carrier by interfacing the adhesive material between the adhesion promoter layer and the semiconductor chip.